



- Drafts
- Pending
- Active
 - L16: (0) memory adj cell and (bit near line\$1 near demarcat\$2)
 - L17: (16) memory adj cell and ((bit near line\$1) with demarcat\$2)
 - L18: (909) memory adj cell and ((bit near line\$1)) and trench\$2 and gate near dielectric
 - L19: (102) ts and diffusion near barrier
- Failed
- Saved
- Favorites
- Tagged (0)
- UDC
- Queue
- Trash

DBs:
USPAT
 Plurals

Default operator
 Highlight all hit terms initially

18 and diffusion near barrier

[SRCH](#) [ISAR](#) [Image](#) [Text](#) [HTML](#)

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
79	<input type="checkbox"/>	<input type="checkbox"/>	US 6492222 B1	20021210	19	Method of dry etching PZT capacitor stack to form high-density ferroelectric memory	438/240	438/239; 438/250
80	<input type="checkbox"/>	<input type="checkbox"/>	US 6485988 B2	20021126	21	Hydrogen-free contact etch for ferroelectric capacitor formation	438/3	257/E21.009; 257/E21.011
81	<input type="checkbox"/>	<input type="checkbox"/>	US 6475855 B1	20021105	22	Method of forming integrated circuitry, method of forming a capacitor and method	438/239	438/250; 438/251
82	<input type="checkbox"/>	<input type="checkbox"/>	US 6465828 B2	20021015	37	Semiconductor container structure with diffusion barrier	257/296	257/301; 257/303
83	<input type="checkbox"/>	<input type="checkbox"/>	US 6440801 B1	20020827	73	Structure for folded architecture pillar memory cell	438/272	257/302; 257/330
84	<input type="checkbox"/>	<input type="checkbox"/>	US 6420272 B1	20020716	9	Method for removal of hard mask used to define noble metal electrode	438/702	216/16; 216/39
85	<input type="checkbox"/>	<input type="checkbox"/>	US 6366489 B1	20020402	26	Bi-state ferroelectric memory devices, uses and operation	365/145	365/149
86	<input type="checkbox"/>	<input type="checkbox"/>	US 6348709 B1	20020219	18	Electrical contact for high dielectric constant capacitors and method for fabricating the	257/311	257/310; 257/751
87	<input type="checkbox"/>	<input type="checkbox"/>	US 6348705 B1	20020219	28	Low temperature process for high density thin film integrated capacitors and	257/295	257/310; 257/E21.272
88	<input type="checkbox"/>	<input type="checkbox"/>	US 6335238 B1	20020101	9	Integrated dielectric and method	438/240	257/77; 257/E21.009
89	<input type="checkbox"/>	<input type="checkbox"/>	US 6259126 B1	20010710	23	Low cost mixed memory integration with FeRAM	257/298	257/303; 257/315